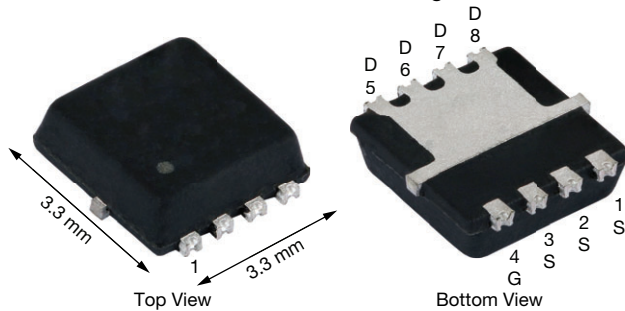


Automotive N-Channel 80 V (D-S) 175 °C MOSFET

PowerPAK® 1212-8W Single


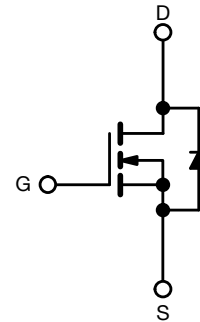
Marking code: Q068

PRODUCT SUMMARY	
V_{DS} (V)	80
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0320
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.0370
I_D (A)	16
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE


RoHS COMPLIANT
 HALOGEN FREE


N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8W
Lead (Pb)-free and halogen-free	SQSA84CENW

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	80	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	$T_C = 25$ °C ^a	16
		$T_C = 125$ °C	11
Continuous source current (diode conduction) ^a	I_S	16	A
Pulsed drain current ^b	I_{DM}	54	
Single pulse avalanche current	I_{AS}	L = 0.1 mH	14
Single pulse avalanche energy			E_{AS}
Maximum power dissipation	P_D	$T_C = 25$ °C	27
		$T_C = 125$ °C	9
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	81	°C/W
Junction-to-case (drain)			

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK1212-8W package may have visible exposed Cu at the end of the lead terminals due to the singulation process. However, the leads also have plated indents on the top and bottom surfaces that promote the formation of a solder fillet compatible with automated optical inspection methods
- Rework conditions: manual soldering with a soldering iron is not recommended



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA	80	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5	2.0	2.5		
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 80 V	-	-	1	μA	
		V _{GS} = 0 V, V _{DS} = 80 V, T _J = 125 °C	-	-	50		
		V _{GS} = 0 V, V _{DS} = 80 V, T _J = 175 °C	-	-	150		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V, V _{DS} ≥ 5 V	10	-	-	A	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 3.5 A	-	0.0227	0.0320	Ω	
		V _{GS} = 10 V, I _D = 3.5 A, T _J = 125 °C	-	-	0.0570		
		V _{GS} = 10 V, I _D = 3.5 A, T _J = 175 °C	-	-	0.0730		
		V _{GS} = 4.5 V, I _D = 3 A	-	0.0263	0.0370		
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 3.5 A	-	20	-	S	
Dynamic ^b							
Input capacitance	C _{iSS}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	-	743	1050	pF	
Output capacitance	C _{oss}		-	111	160		
Reverse transfer capacitance	C _{rSS}		-	8	12		
Total gate charge ^c	Q _g	V _{GS} = 10 V, V _{DS} = 40 V, I _D = 5 A	-	14.1	22	nC	
Gate-source charge ^c	Q _{gs}		-	2.6	-		
Gate-drain charge ^c	Q _{gd}		-	2.6	-		
Gate resistance	R _g	f = 1 MHz	0.35	0.72	1.20	Ω	
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 40 V, R _L = 10 Ω I _D ≅ 4 A, V _{GEN} = 10 V, R _g = 1 Ω	-	7	12	ns	
Rise time ^c	t _r		-	3	6		
Turn-off delay time ^c	t _{d(off)}		-	15	25		
Fall time ^c	t _f		-	3	6		
Source-Drain Diode Ratings and Characteristic ^b							
Pulsed current ^a	I _{SM}		-	-	54	A	
Forward voltage	V _{SD}	I _F = 3.5 A, V _{GS} = 0 V	-	0.8	1.1	V	
Body diode reverse recovery time	t _{rr}	I _F = 5 A, di/dt = 100 A/μs	-	27	54	ns	
Body diode reverse recovery charge	Q _{rr}		-	23	46	nC	
Reverse recovery fall time	t _a		-	19	-	ns	
Reverse recovery rise time	t _b		-	8	-		
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.39	-	A

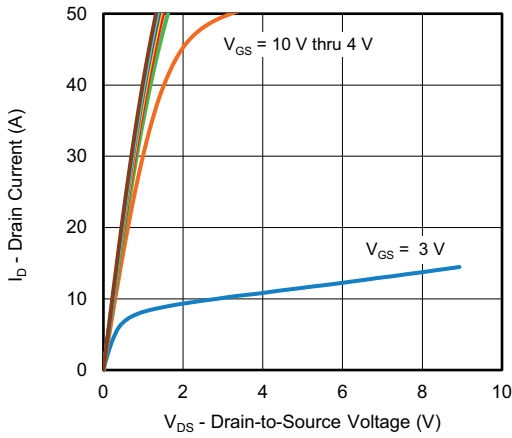
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

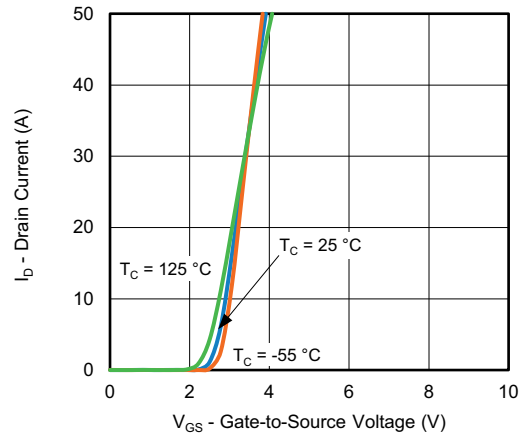
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



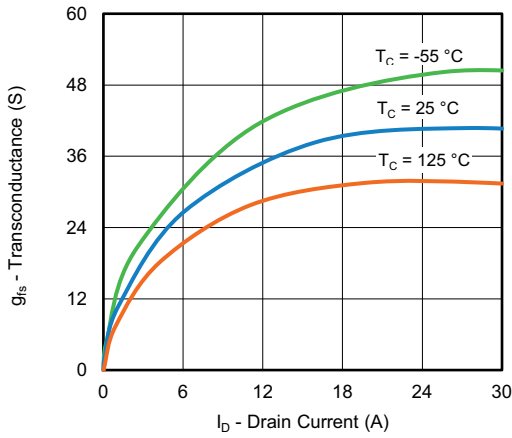
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



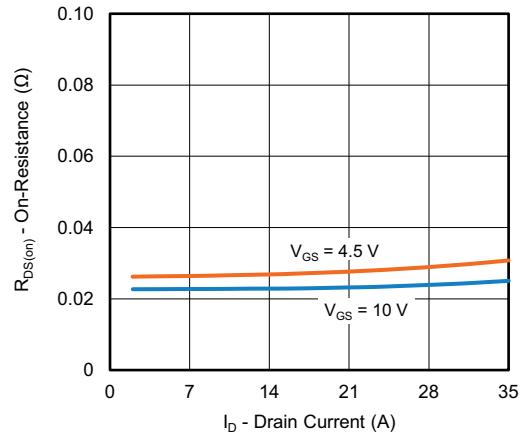
Output Characteristics



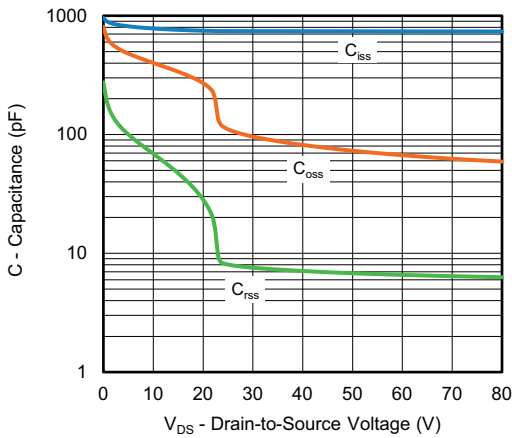
Transfer Characteristics



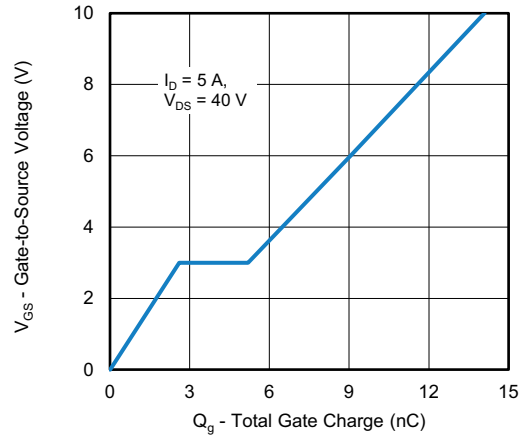
Transconductance



On-Resistance vs. Drain Current



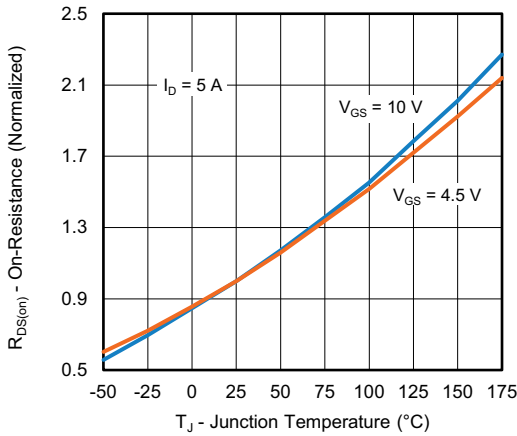
Capacitance



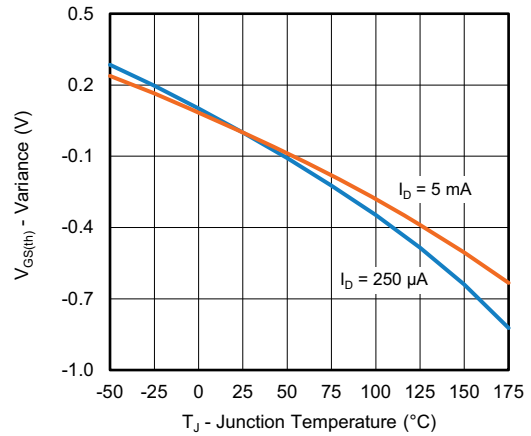
Gate Charge



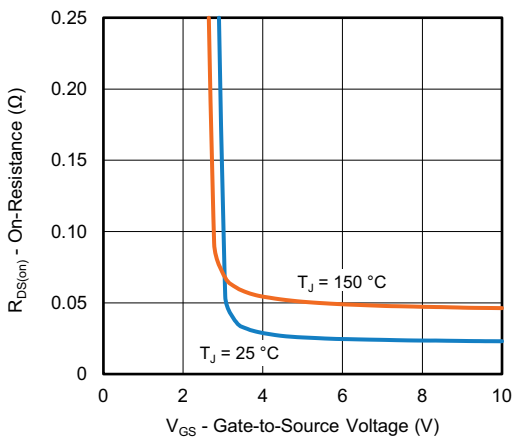
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



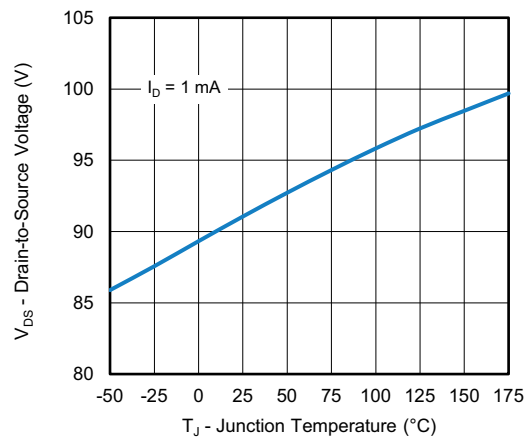
On-Resistance vs. Junction Temperature



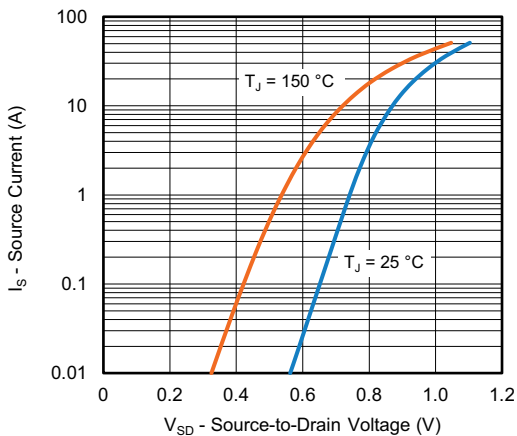
Threshold Voltage



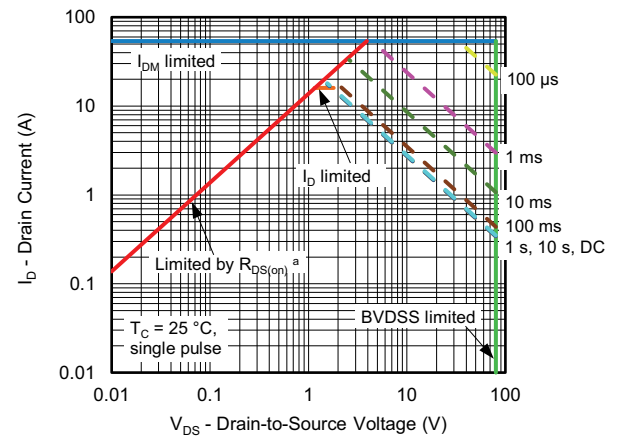
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



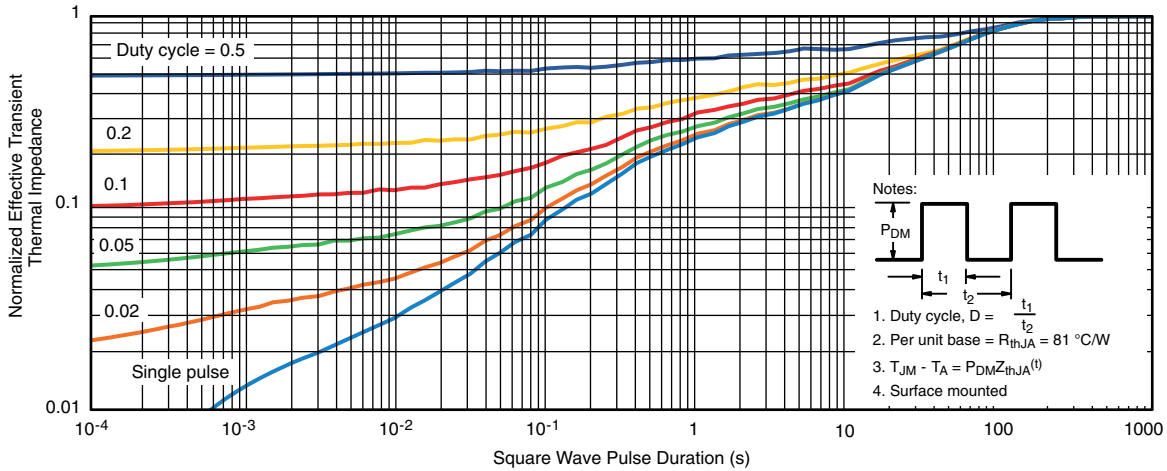
Safe Operating Area

Note

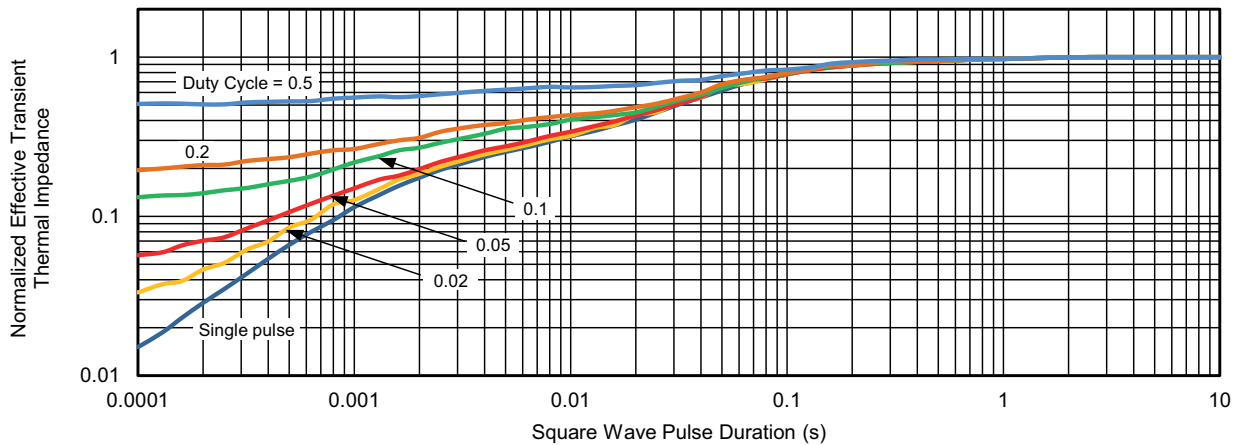
- a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^\circ\text{C}$)
- are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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